

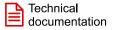






SN74AHC1G14





# JAJSRG4S - MARCH 1996 - REVISED FEBRUARY 2024

# SN74AHC1G14 シングル・シュミット・トリガ・インバ

# 1 特長

- 動作範囲:2V~5.5V
- 最大 t<sub>od</sub> 10ns (5V 時)
- 低消費電力、最大 I<sub>CC</sub> 10μA
- ±8mA の出力駆動能力 (5V 時)
- JESD 17 準拠で 250mA 超のラッチアップ性能

# 2 アプリケーション

- バーコード・スキャナ
- ケーブル・ソリューション
- eBook (電子書籍)
- 組み込み用 PC
- フィールド・トランスミッタ:温度センサ、圧力 センサ
- 指紋認証
- HVAC:暖房、換気、空調
- ネットワーク接続ストレージ (NAS)
- サーバーのマザーボードおよび PSU
- ソフトウェア定義無線 (SDR)
- テレビ:高解像度 (HDTV)、LCD、デジタル
- ビデオ通信システム
- ワイヤレス・データ・アクセス・カード、ヘッド セット、キーボード、マウス、LAN カード

#### 3 概要

SN74AHC1G14 デバイスはシングル・インバータ・ ゲートです。このデバイスは、ブール関数 Y= A を実 行します。

#### パッケージ情報

部品番号	パッケージ (1)	パッケージ・サイズ (2)	本体サイズ <sup>(3)</sup>
	DBV (SOT-23、5)	2.8mm × 2.8mm	2.9mm × 1.6mm
SN74AHC1G14	DCK (SC-70、5)	2mm × 2.1mm	2mm × 1.25mm
	DRL (SOT-553、5)	1.6mm × 1.6mm	1.6mm × 1.2mm

- (1) 利用可能なすべてのパッケージについては、データシートの 末尾にある注文情報を参照してください。
- パッケージ・サイズ (長さ×幅) は公称値であり、該当する場 (2) 合はピンも含まれます。
- 本体サイズ (長さ×幅) は公称値であり、ピンは含まれませ





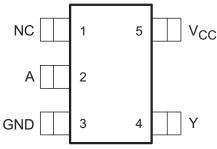
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English Data Sheet: SCLS321



# **4 Pin Configuration and Functions**



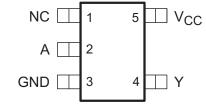


図 4-2. DCK Package 5-Pin SC70 Top View

図 4-1. DBV Package 5-Pin SOT-23 Top View

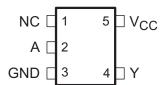


図 4-3. DRL Package 5-Pin SOT Top View

表 4-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NO.	NAME	ITPE\'	DESCRIPTION
1	NC	_	No connect
2	A	I	Data Input
3	GND	_	Ground
4	Y	0	Data Output
5	VCC	_	Power

(1) Signal Types: I = Input, O = Output, I/O = Input or Output



# **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	7	V
VI	Input voltage <sup>(2)</sup>		-0.5	7	V
Vo	Output voltage <sup>(2)</sup>		-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-20	mA
I <sub>OK</sub>	Output clamp current	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
Io	Continuous output current	$V_{O} = 0$ to $V_{CC}$		±25	mA
	Continuous current through V <sub>CC</sub> or GND			±50	mA
Tj	Maximum junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 5.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±1500	V
V <sub>(ESD)</sub>	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	±1000	

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT	
V <sub>CC</sub>	Supply voltage		2	5.5	V	
VI	Input voltage		0	5.5	V	
Vo	Output voltage		0	V <sub>CC</sub>	V	
		V <sub>CC</sub> = 2 V		-50	μA	
I <sub>OH</sub>	High-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		-4	mA	
		$V_{CC} = 5 V \pm 0.5 V$		-8	ША	
		V <sub>CC</sub> = 2 V		50	μΑ	
I <sub>OL</sub>	Low-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		4		
		$V_{CC} = 5 V \pm 0.5 V$		8	mA	
T <sub>A</sub>	Operating free-air temperature		-40	125	°C	

<sup>(1)</sup> All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

Product Folder Links: SN74AHC1G14

<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



## **5.4 Thermal Information**

			SN74AHC1G14		
	THERMAL METRIC <sup>(1)</sup>	DBV (SOT-23)	DCK (SC70)	DRL (SOT)	UNIT
		5 PINS	5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	278	289.2	271.8	°C/W
R <sub>0</sub> JC(top)	Junction-to-case (top) thermal resistance	180.5	205.8	116.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	184.4	176.2	89.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	115.4	117.6	17.3	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	183.4	175.1	89.4	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bot) thermal resistance	N/A	N/A	N/A	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

## 5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	TA	= 25°C		T <sub>A</sub> = -4	40°C to 85°C		OMMENDED 10°C to 125°C	UNIT
		CONDITIONS		MIN	TYP	MAX	MIN	TYP MAX	MIN	TYP MAX	
			3 V	1.2		2.2	1.2	2.2	1.2	2.2	
$V_{T+}$	Positive-going input threshold voltage		4.5 V	1.75		3.15	1.75	3.15	1.75	3.15	\ \ \
	un senera venage		5.5 V	2.15		3.85	2.15	2.85	2.15	3.85	
	Negative-going		3 V	0.9		1.9	0.9	1.9	0.9	1.9	
$V_{T-}$	input threshold		4.5 V	1.35		2.75	1.35	2.75	1.35	2.75	V
	voltage		5.5 V	1.65		3.35	1.65	3.35	1.65	3.35	
			3 V	0.3		1.2	0.3	1.2	0.25	1.2	
$\Delta V_T$	Hysteresis (V <sub>T+</sub> – V <sub>T–</sub> )		4.5 V	0.4		1.4	0.4	1.4	0.35	1.4	\ \ \ \ \
	V 1-)		5.5 V	0.5		1.6	0.5	1.6	0.45	1.6	
		I <sub>OH</sub> = -50 μA	2 V	1.9	2		1.9		1.9		
			3 V	2.9	3		2.9		2.9		
V <sub>OH</sub>	High level output voltage		4.5 V	4.4	4.5		4.4		4.4		\ \ \
	vollago	I <sub>OH</sub> = -4 mA	3 V	2.58			2.48		2.4		
		I <sub>OL</sub> = -8 mA	4.5 V	3.94			3.8		3.7		
		I <sub>OH</sub> = 50 μA	2 V			0.1		0.1		0.1	
			3 V			0.1		0.1		0.1	
V <sub>OL</sub>	Low level output voltage		4.5 V			0.1		0.1		0.1	\ \ \
	vollago	I <sub>OH</sub> = 4 mA	3 V			0.36		0.44		0.55	
		I <sub>OL</sub> = 8 mA	4.5 V			0.36		0.44		0.55	
II	Input leakage current	V <sub>I</sub> = 5.5 V or GND	0 V to 5.5 V			±0.1		±1		±1	μА
I <sub>CC</sub>	Supply current	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			1		10		10	μA
Ci	Input Capacitance	$V_I = V_{CC}$ or GND	5 V		2	10		10		10	pF

# 5.6 Switching Characteristics, $V_{CC}$ = 3.3 V $\pm$ 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T <sub>A</sub> = 25	5°C	T <sub>A</sub> = -40°C	to 85°C	RECOMME T <sub>A</sub> = -40° 125°	°C to	UNIT		
				TYP	MAX	MIN	MAX	MIN	MAX			
t <sub>PLH</sub>	Α	V	C <sub>1</sub> = 15 pF	8.3	12.8	1	15	1	16	ns		
t <sub>PHL</sub>	^	T	'	ı	OL = 13 pi	8.3	12.8	1	15	1	16	ns
t <sub>PLH</sub>	Α		C <sub>1</sub> = 50 pF	10.8	16.3	1	18.5	1	19.5	ns		
t <sub>PHL</sub>	Α	<b>1</b>	OL = 30 pr	10.8	16.3	1	18.5	1	19.5	ns		

# 5.7 Switching Characteristics, $V_{CC}$ = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

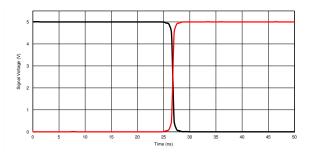
PARAMETER	FROM TO OUTPUT (INPUT) (OUTPUT) CAPACITANCE		T <sub>A</sub> = 2	25°C	T <sub>A</sub> = -40°	C to 85°C	RECOMME T <sub>A</sub> = -40°C t		UNIT	
	(INFOI)	(001701)	CAFACITANCE	TYP	MAX	MIN	MAX	MIN	MAX	
t <sub>PLH</sub>	A or B	V	C <sub>1</sub> = 15 pF	5.5	8.6	1	10	1	11	ns
t <sub>PHL</sub>	AUID	Ĭ	CL = 15 pr	5.5	8.6	1	10	1	11	ns
t <sub>PLH</sub>	A or B		C <sub>1</sub> = 50 pF	7	10.6	1	12	1	11	ns
t <sub>PHL</sub>	A OI B	Ĭ	CL = 50 pr	7	10.6	1	12	1	11	ns

# 5.8 Operating Characteristics

 $V_{CC}$  = 5 V,  $T_A$  = 25°C

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C <sub>pd</sub>	Power dissipation capacitance	No load, f = 1 MHz	9	pF

# **5.9 Typical Characteristics**



 $T_A = 25^{\circ}C, V_A = 5 V$ 

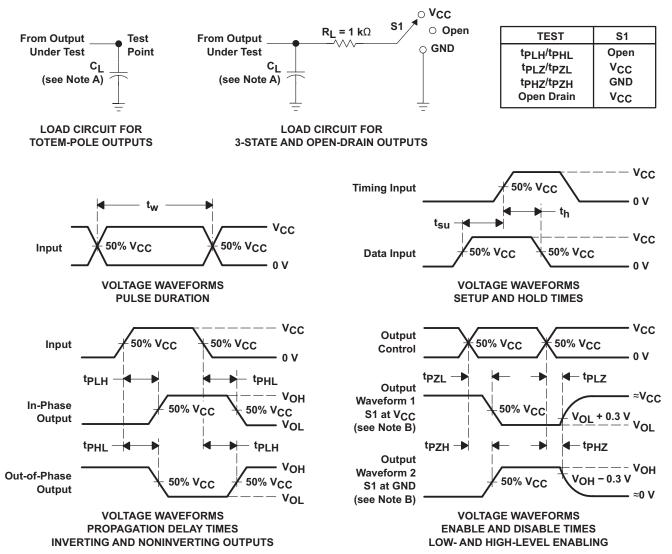
☑ 5-1. Response Time vs Output Voltage

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#### **6 Parameter Measurement Information**



- A. C<sub>L</sub> includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O = 50 \Omega$ ,  $t_r \leq$  3 ns,  $t_f \leq$  3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

図 6-1. Load Circuit and Voltage Waveforms

資料に関するフィードバック(ご意見やお問い合わせ) を送信



# 7 Detailed Description

## 7.1 Overview

The SN74AHC1G14 device is a single inverter gate. The device performs the Boolean function  $Y = \overline{A}$ .

The device functions as an independent inverter gate, but because of the Schmitt action, gates may have different input threshold levels for positive-  $(V_{T+})$  and negative-going  $(V_{T-})$  signals.

## 7.2 Functional Block Diagram

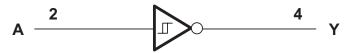


図 7-1. Logic Diagram (Positive Side)

# 7.3 Feature Description

The SN74AHC1G14 device has a wide operating  $V_{CC}$  range of 2 V to 5.5 V, which allows it to be used in a broad range of systems. The low propagation delay allows fast switching and higher speeds of operation. In addition, the low-power consumption makes this device a good choice for portable and battery power-sensitive applications.

#### 7.4 Device Functional Modes

表 7-1 lists the functional modes for SN74AHC1G14.

表 7-1. Function Table

INPUT <sup>(1)</sup> A	OUTPUT <sup>(2)</sup> Y
Н	L
L	Н

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
- (2) H = Driving High, L = Driving Low, Z = High Impedance State

# 8 Application and Implementation

注

以下のアプリケーション情報は、TIの製品仕様に含まれるものではなく、TIではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

#### 8.1 Application Information

Physically interactive interface elements like push buttons or rotary knobs offer simple and easy ways to interact with an electronic system. Many of these physical interface elements often have issues with bouncing, or where the physical conductive contact can connect and disconnect multiple times during a button push or release. This bouncing can cause one or more faulty transient signals to be passed during this transitional period. These faulty signals can be observed in many common applications, for example, a television remote with bouncing error can adjust the TV channel multiple times despite the button being pushed only once. To mitigate these faulty signals, we can use a Schmitt-trigger, or a device with hysteresis, to remove these faulty signals. Hysteresis allows a device to *remember* its history, and in this case, the SN74AHC1G14 uses this memory to debounce the signal of the physical element, or filter the faulty transient signals and pass only the valid signal each time the element is used. In this example, we show a push-button signal passed through an SN74AHC1G14 that is debounced and inverted to the microprocessor for push detection.

#### 8.2 Typical Application

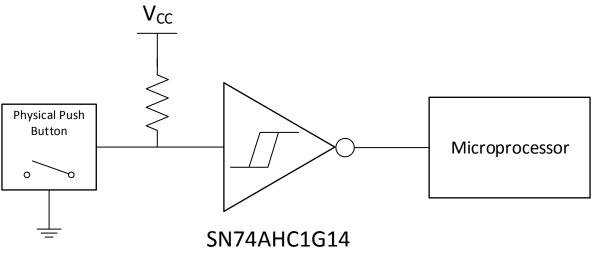


図 8-1. Switch Debouncer

#### 8.2.1 Design Requirements

The SN74AHC1G14 device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The SN74AHC1G14 allows for performing logical Boolean functions with hysteresis using digital signals. All input signals must remain as close as possible to either 0 V or VCC for optimal operation.

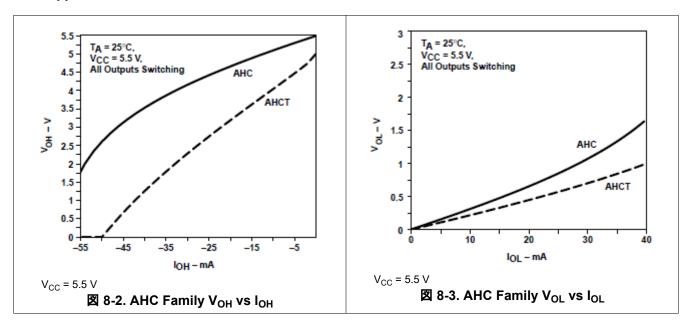
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#### 8.2.2 Detailed Design Procedure

- 1. Recommended input conditions:
  - For rise time and fall time specifications, see  $\Delta t/\Delta v$  in the  $\pm 2/2 = 2/5.3$  table.
  - For specified high and low levels, see  $V_{IH}$  and  $V_{IL}$  in the  $\pm 2993 \times 5.3$  table.
  - Inputs and outputs are overvoltage tolerant and can therefore go as high as 5.5 V at any valid V<sub>CC</sub>.
- 2. Recommended output conditions:
  - Load currents must not exceed ±50 mA.
- 3. Frequency selection criterion:
  - The effects of frequency upon the power consumption of the device can be studied in CMOS Power Consumption and CPD Calculation, SCAA035.
  - Added trace resistance and capacitance can reduce maximum frequency capability; follow the layout practices listed in the セクション 8.4.1 section.

#### 8.2.3 Application Curves



## 8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the  $\angle 253 \times 5.3$  table.

Each  $V_{CC}$  terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F bypass capacitor is recommended. If multiple pins are labeled  $V_{CC}$ , then a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each  $V_{CC}$  because the  $V_{CC}$  pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example  $V_{CC}$  and  $V_{DD}$ , a 0.1- $\mu$ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1  $\mu$ F and 1  $\mu$ F are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

#### 8.4 Layout

#### 8.4.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed

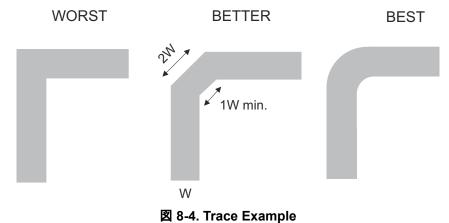
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capacitance and self-inductance of the trace, which results in the reflection. Not all PCB traces can be straight; therefore some traces must turn corners. 🗵 8-4 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

#### 8.4.1.1 Layout Example



資料に関するフィードバック(ご意見やお問い合わせ)を送信

11



# 9 Device and Documentation Support

# 9.1 Documentation Support (Analog)

#### 9.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- CMOS Power Consumption and CPD Calculation, SCAA035
- Selecting the Right Texas Instruments Signal Switch, SZZA030

#### 9.2 サポート・リソース

テキサス・インスツルメンツ E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

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#### 9.3 Trademarks

テキサス・インスツルメンツ E2E<sup>™</sup> is a trademark of Texas Instruments. すべての商標は、それぞれの所有者に帰属します。

#### 9.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

#### 9.5 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

# 10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

# Changes from Revision R (October 2023) to Revision S (February 2024)

Page

#### Changes from Revision Q (February 2014) to Revision R (October 2023)

Pag

- Updated thermal values for DCK package: R0JA = 287.6 to 289.2, all values in °C/W ......5
- Added thermal values for DCK package: RθJC(top) = 205.8, RθJB = 176.2, ΨJT = 117.6, ΨJB = 175.1,
   RθJC(bot) = N/A, all values in °C/W

# 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

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#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHC1G14DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(A143, A14G, A14J, A14L, A14S)	Samples
SN74AHC1G14DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A14G	Samples
SN74AHC1G14DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A14G	Samples
SN74AHC1G14DCK3	ACTIVE	SC70	DCK	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	AFY	Samples
SN74AHC1G14DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(AF3, AFG, AFJ, AF L, AFS)	Samples
SN74AHC1G14DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF3	Samples
SN74AHC1G14DCKTE4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF3	Samples
SN74AHC1G14DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AF3	Samples
SN74AHC1G14DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	AFS	Samples
SN74AHC1G14DRLRG4	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	AFS	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



# **PACKAGE OPTION ADDENDUM**

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- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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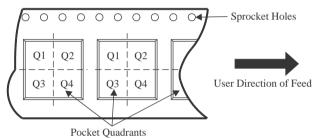
## TAPE AND REEL INFORMATION



# TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

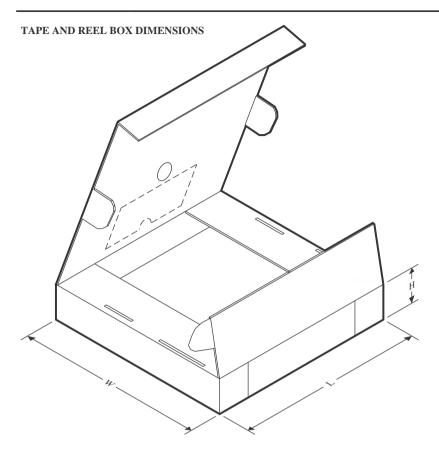


#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G14DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G14DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AHC1G14DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AHC1G14DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G14DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G14DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3



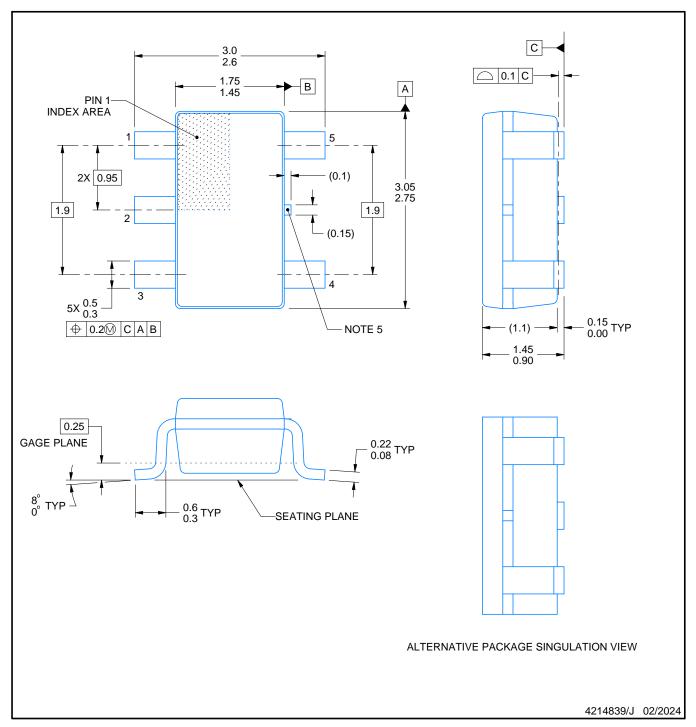
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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHC1G14DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74AHC1G14DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHC1G14DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHC1G14DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74AHC1G14DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHC1G14DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74AHC1G14DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0



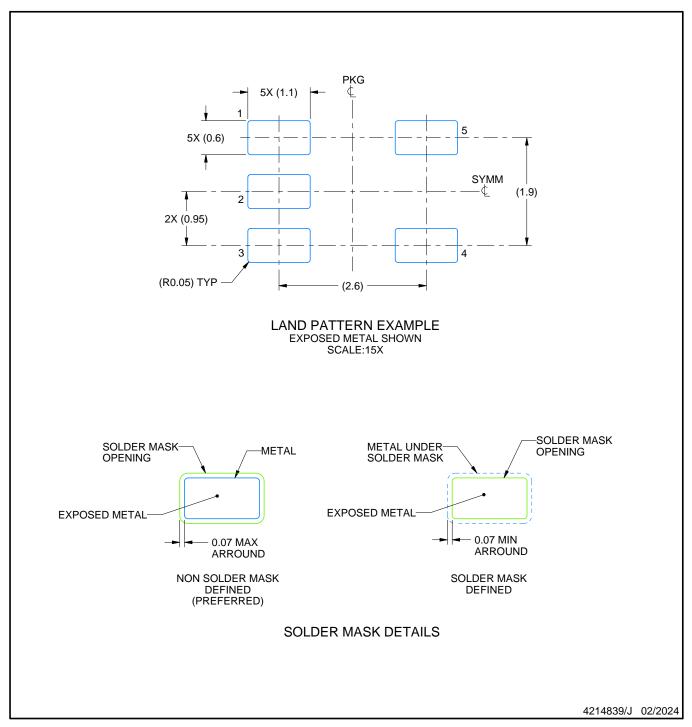


#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



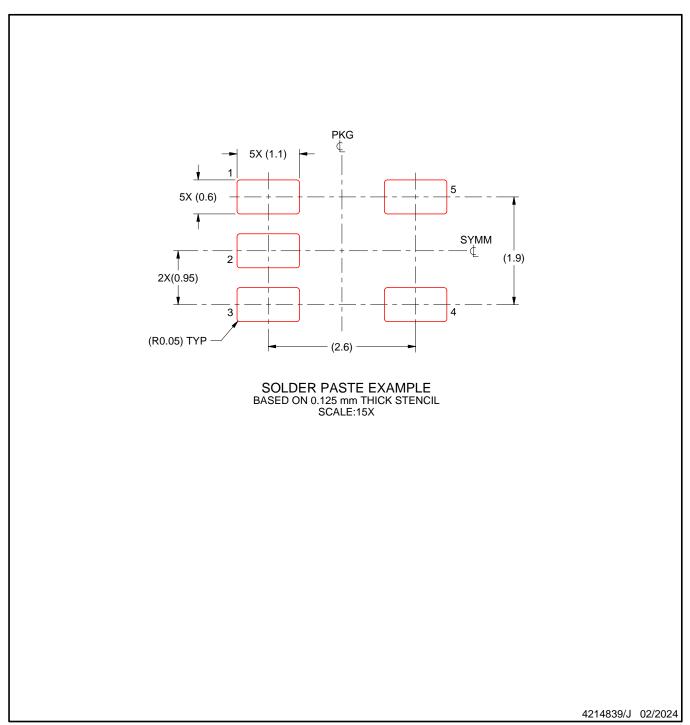


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



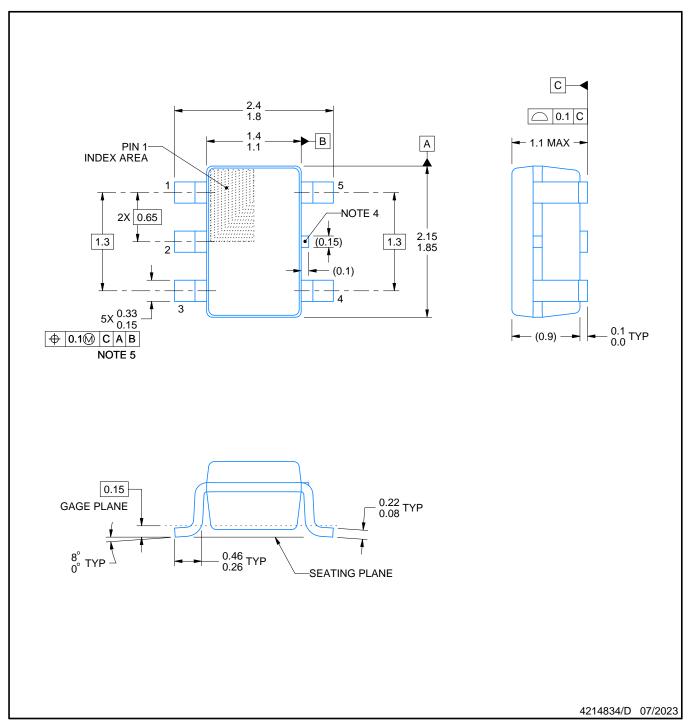


NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







#### NOTES:

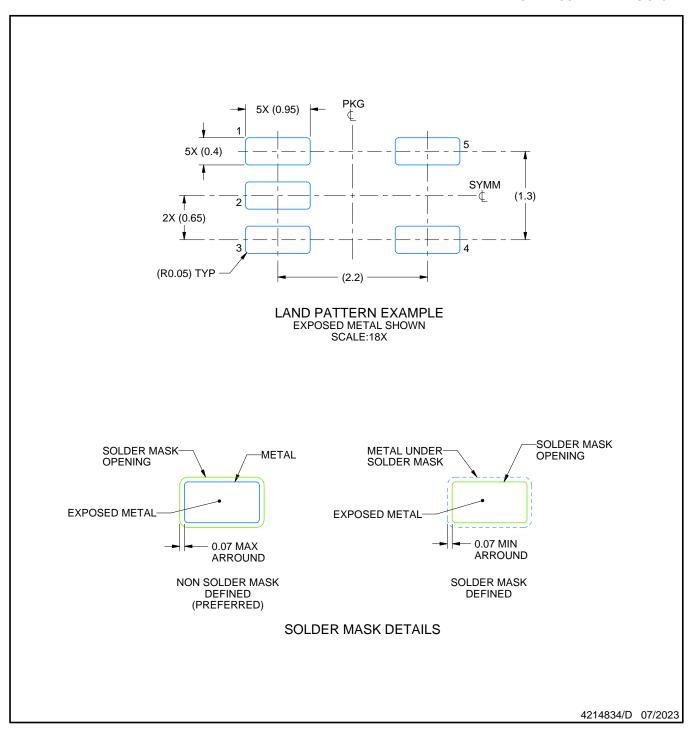
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.

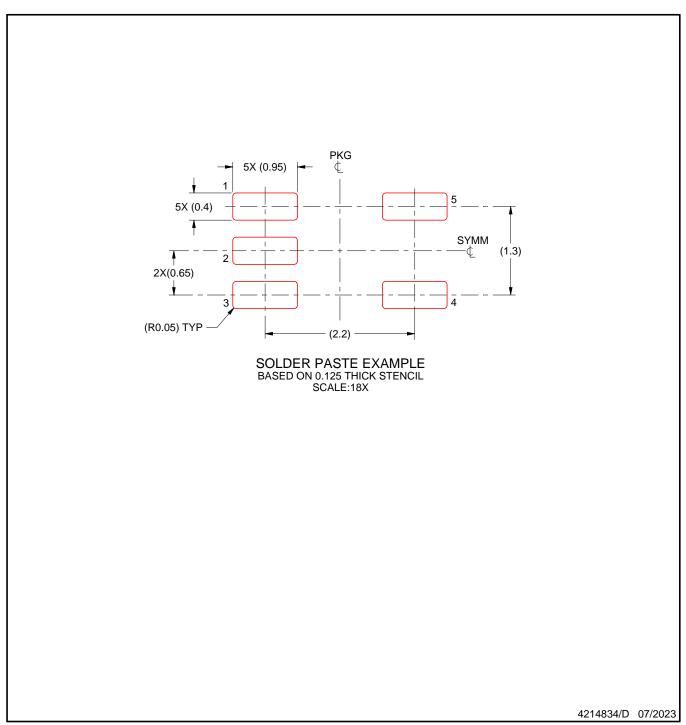




NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





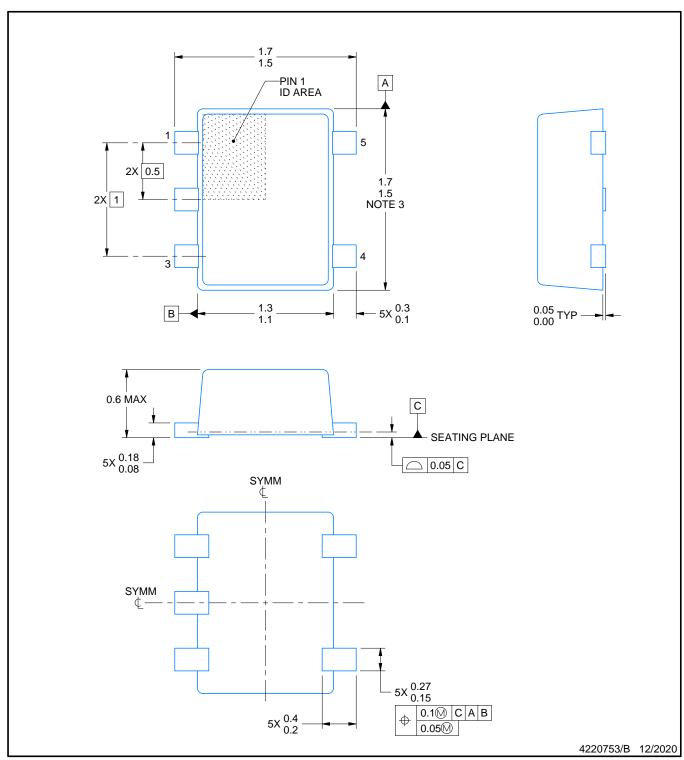
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





PLASTIC SMALL OUTLINE



#### NOTES:

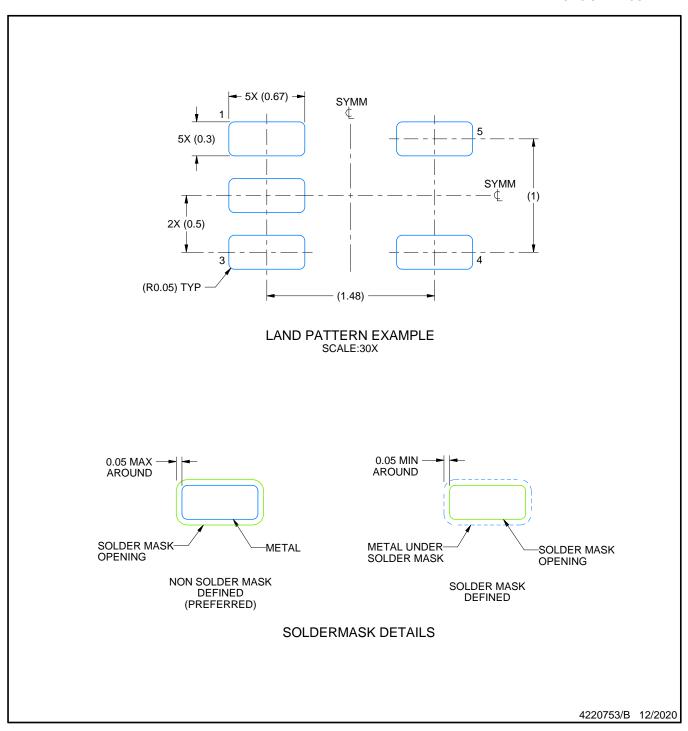
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
  4. Reference JEDEC registration MO-293 Variation UAAD-1



PLASTIC SMALL OUTLINE

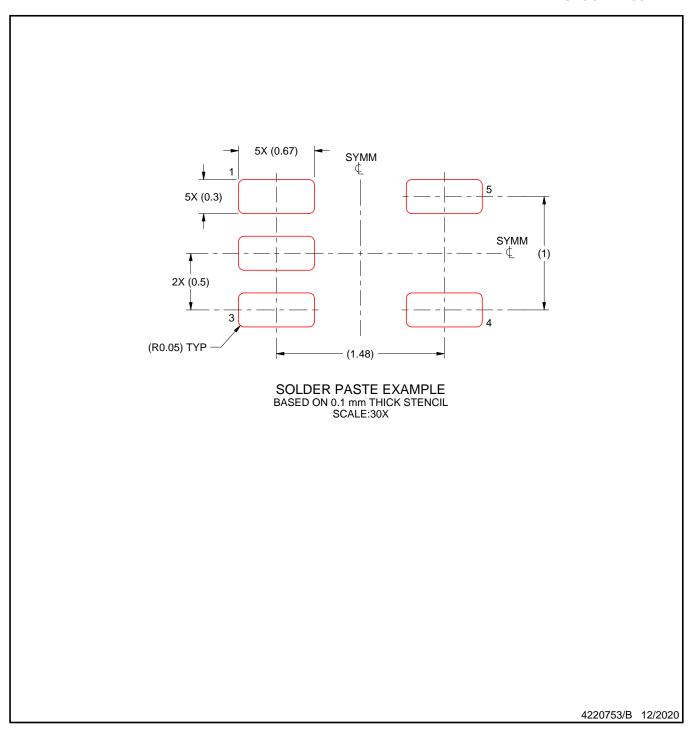


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)



<sup>7.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

<sup>8.</sup> Board assembly site may have different recommendations for stencil design.

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